Product data sheet

1. General description

NPN low V_{CEsat} transistor in a SOT223 (SC-73) small Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS9110Z

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- · High-voltage DC-to-DC conversion
- High-voltage MOSFET gate driving
- High-voltage motor control
- · High-voltage power switches (e.g. motors, fans)
- Automotive applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	100	V
I _C	collector current		-	-	1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	3	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 1 A; I_B = 100 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	160	200	mΩ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	С
2	С	collector		
3	Е	emitter		B —
4	С	collector	∃1 ∃2 ∃3	Ė
			SC-73 (SOT223)	sym123

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
PBSS8110Z-Q		plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body	SOT223				

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS8110Z-Q	PB8110

8. Limiting values

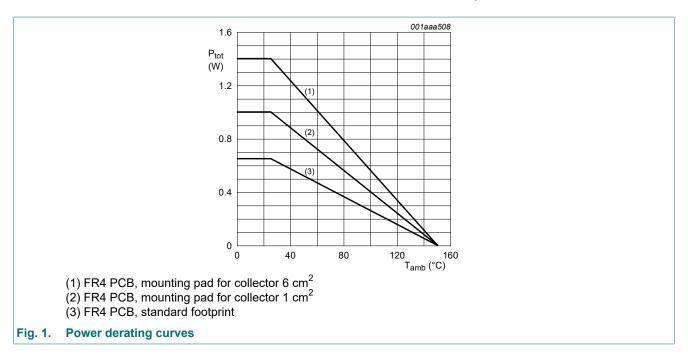
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	120	V
V _{CEO}	collector-emitter voltage	open base		-	100	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
I _C	collector current			-	1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	3	А
I _B	base current			-	0.3	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.65	W
			[2]	-	1	W
			[3]	-	1.4	W
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

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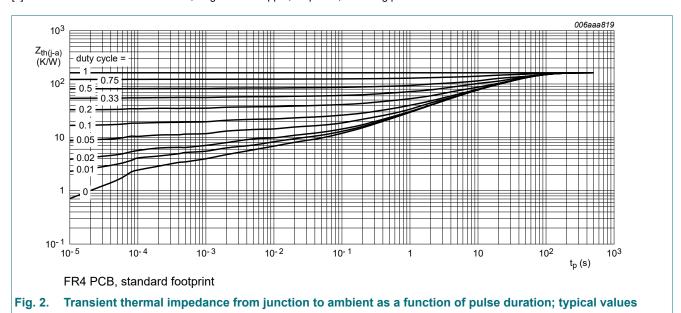


9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uη-α)		to ambient [2	[1]	-	-	192	K/W
	junction to ambient		[2]	-	-	125	K/W
			[3]	-	-	89	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	17	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm². Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².



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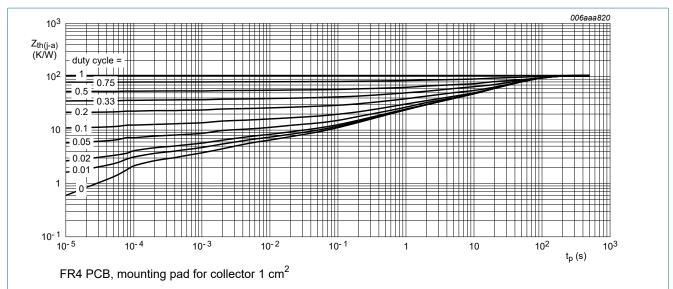


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

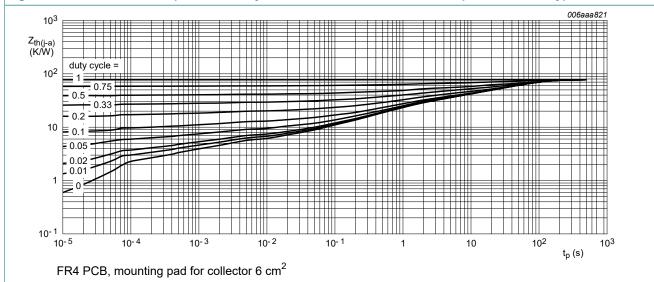


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

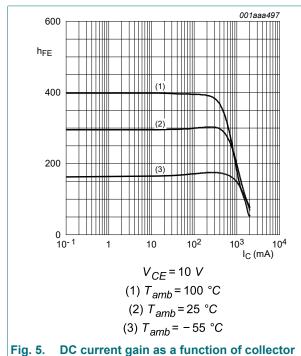
10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 80 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 80 V; I _E = 0 A; T _j = 150 °C	-	-	50	μΑ
I _{CES}	collector-emitter cut-off current	V _{CE} = 80 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = 4 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 10 V; I _C = 1 mA; T _{amb} = 25 °C	150	-	-	
		V_{CE} = 10 V; I_{C} = 250 mA; T_{amb} = 25 °C	150	-	500	
		V_{CE} = 10 V; I_{C} = 0.5 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	100	-	-	
		V_{CE} = 10 V; I_{C} = 1 A; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	80	-	-	

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Symbol	Parameter	Conditions	Mi	п Тур	Max	Unit
V _{CEsat}	collector-emitter	I _C = 100 mA; I _B = 10 mA; T _{amb} = 25 °C	-	-	40	mV
	saturation voltage	I_C = 500 mA; I_B = 50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	120	mV
		I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le$	-	-	200	mV
R _{CEsat}	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	160	200	mΩ
V _{BEsat}	base-emitter saturation voltage		-	-	1.05	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 10 V; I_{C} = 1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	0.9	V
t _d	delay time	V _{CC} = 10 V; I _C = 0.5 A; I _{Bon} = 0.025 A;	-	25	-	ns
t _r	rise time	I _{Boff} = -0.025 A; T _{amb} = 25 °C	-	220	-	ns
t _{on}	turn-on time		-	245	-	ns
t _s	storage time		-	365	-	ns
t _f	fall time		-	185	-	ns
t _{off}	turn-off time		-	550	-	ns
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 50 mA; f = 100 MHz; T_{amb} = 25 °C	10	0 -	-	MHz
C _c	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	-	7.5	pF



001aaa496 2 I_C (A) I_{B} (mA) = 35 31.5 1.6 24.5 17.5 1.2 14 -10.5 8.0 3.5 0.4 0 4 V_{CE} (V) 5 0 1 2 3 T_{amb} = 25 °C

Fig. 6. Collector current as a function of collectoremitter voltage; typical values

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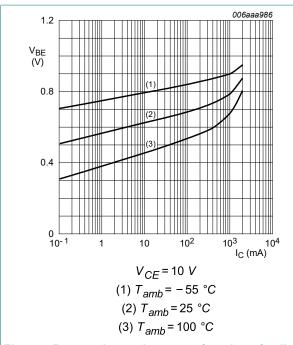


Fig. 7. Base-emitter voltage as a function of collector current; typical values

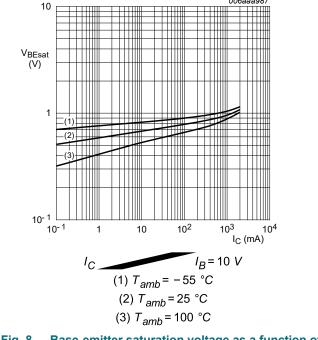


Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

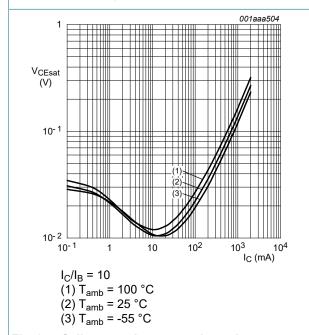


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

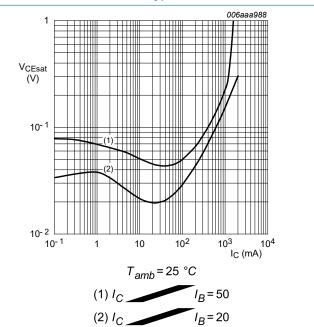
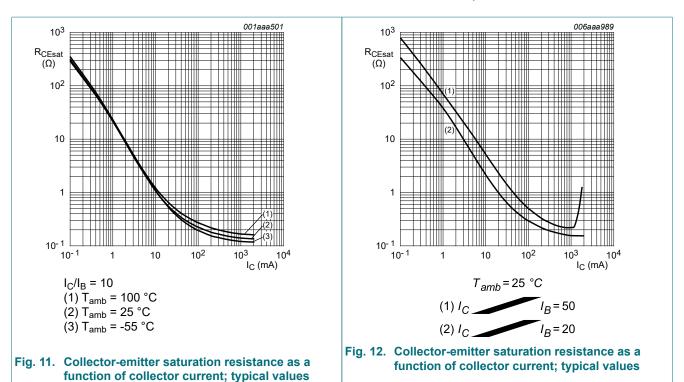
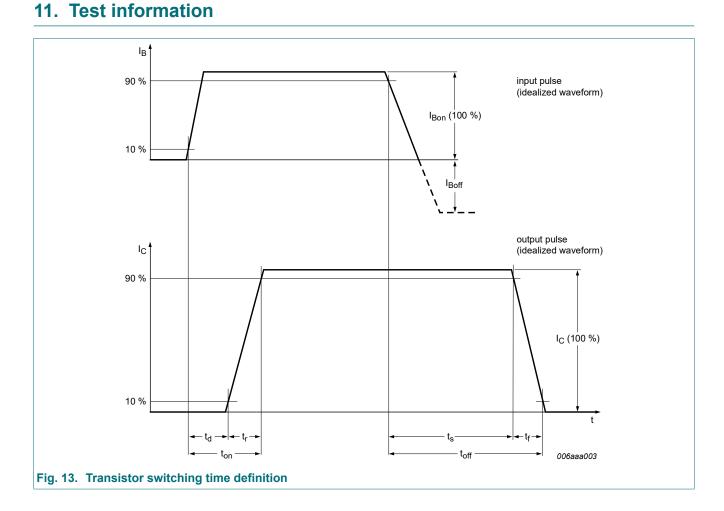


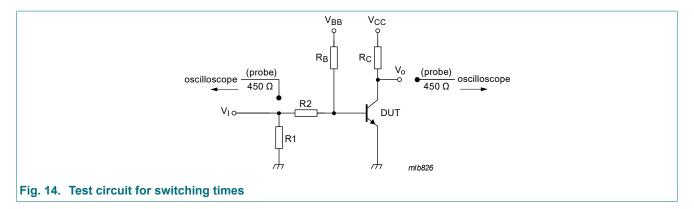
Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

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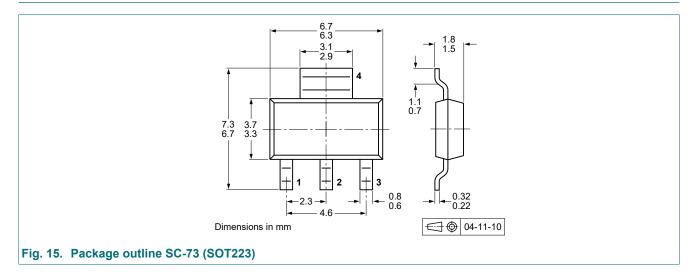
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Quality information

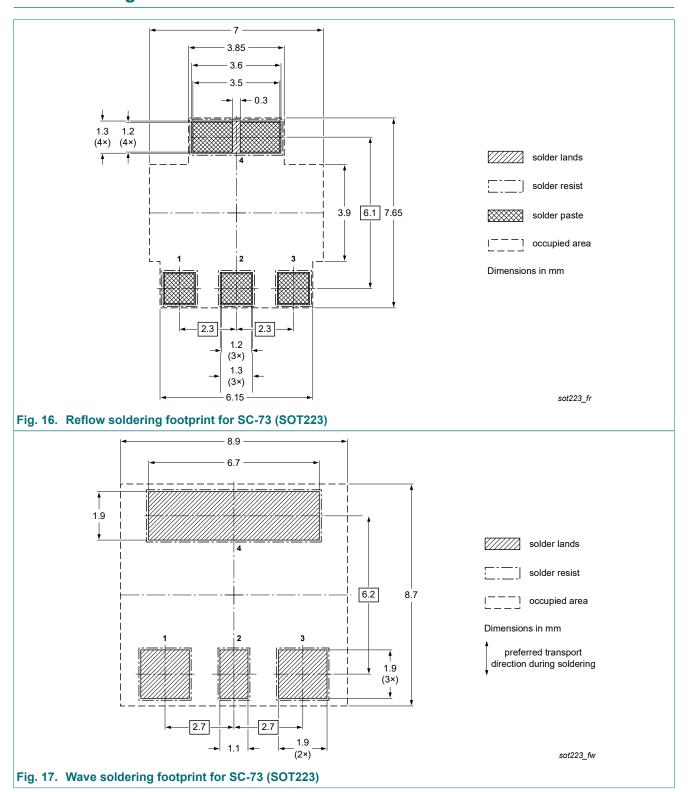
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS8110Z-Q v.3	20250729	Product data sheet	-	-

100 V, 1 A NPN low VCesat transistor

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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